Everspin Launches New Generation of Unified Memory for Embedded Systems

March 10, 2026

UNISYST MRAM unifies code storage and data memory in a high-density, non-volatile architecture for edge AI, industrial and mission-critical designs

CHANDLER, Ariz.--(BUSINESS WIRE)--Mar. 10, 2026-- Everspin Technologies, Inc. (NASDAQ: MRAM), the world's leading developer and manufacturer of magnetoresistive random access memory (MRAM) persistent memory solutions, today announced the *UNISYST* MRAM family, a new generation of unified memory designed to fundamentally change how embedded systems store and access code and data.

"System designers are running into the physical and performance limits of NOR flash, especially as process nodes move below 40 nanometers and workloads become more demanding," said Sanjeev Aggarwal, president and CEO of Everspin Technologies. "With *UNISYST*, we are extending our MRAM roadmap to higher densities while giving customers a practical way to start with *PERSYST* today and migrate to a code-and-data MRAM architecture as soon as it is available."

UNISYST is a unified code-and-data MRAM architecture that bridges traditional configuration memory and higher-density persistent storage, extending MRAM into traditional NOR flash applications where superior performance, endurance and reliability are valued. Built as a natural extension of Everspin's existing *PERSYST* MRAM platform, *UNISYST* gives customers a practical, simple migration path from today's serial MRAM devices to higher-density unified memory without requiring changes to system architecture or software.

Everspin will initially offer the *UNISYST* family in densities ranging from 128 megabits to 2 gigabits, using a standard xSPI interface operating up to octal SPI at 200MHz. The devices are planned to feature AEC-Q100 Grade 1 qualification and minimum 10-year data retention at extreme temperature, supporting demanding environments across automotive, aerospace, industrial and edge AI applications.

"As generative AI models move from the cloud to embedded systems, we're suddenly dealing with assets that are tens or even hundreds of megabytes in size," said Kwabena W. Agyeman, President and Co-founder of OpenMV. "Storing those models is only part of the challenge — updating them quickly during development and deployment is equally important. High-speed, non-volatile Everspin *UNISYST* MRAM changes what's practical for edge AI systems by removing the write bottlenecks associated with traditional flash."

UNISYST delivers high-bandwidth read and write speeds in a non-volatile memory device, enabling fast boot, rapid updates and predictable performance without the tradeoffs of traditional flash-based designs. By combining high-speed access with persistent storage, *UNISYST* supports software-defined systems that require frequent reconfiguration while maintaining data integrity across power cycles.

Everspin MRAM has been deployed in mission-critical storage applications for nearly two decades, valued for its endurance and reliability. *UNISYST* builds on Everspin's proven MRAM foundation with capabilities designed to support more complex, software-defined systems:

- Code-and-data MRAM architecture designed as a next-generation alternative to other non-volatile memory
- Standard xSPI interface operating up to octal SPI at 200MHz
- Read bandwidth of up to 400 MB/s and write bandwidth of approximately 90 MB/s, over 400 times faster than NOR flash
- Write endurance up to 10 times higher than typical NOR
- AEC-Q100 Grade 1 qualification and minimum 10-year data retention for high-reliability designs

UNISYST is aimed at applications where non-volatile memory must combine high bandwidth, high endurance and predictable behavior over temperature and time. Target use cases include:

- AI at the edge: Fast AI weight updates, critical storage at the edge, local code-and-data storage for workloads that need fast boot, rapid reconfiguration and non-volatile operation close to the sensor, with the ability to execute in place removing the need for multiple system memories
- Military and aerospace: Field-programmable gate array (FPGA) configuration and code storage for mission-critical systems, including low-Earth orbit satellites and other platforms that require frequent over-the-air updates
- Automotive: Control, logging and configuration memory in systems that must meet Grade 1 temperature requirements and long-term data retention

- Industrial and casino gaming: High-traffic logging and configuration in environments that demand fast writes, long endurance and persistent storage supporting data logging

The launch of *UNISYST* represents a platform-level expansion of Everspin's MRAM portfolio, extending the company's role from a niche memory supplier to a mainstream memory player serving a multibillion-dollar market. By unifying code storage and data memory, Everspin is addressing the growing demands of software-defined systems that require faster boot times, frequent updates and predictable behavior over long operating lifetimes.

Engineering samples of *UNISYST* are expected to be available in the fourth quarter of 2026, with additional densities and options to follow.

The *UNISYST* product line will be formally launched at Embedded World 2026, where Everspin will highlight how unified memory architectures can simplify system design and enable higher-performance platforms. Attendees can meet with Everspin at Hall 4, Booth 360 to learn more about *UNISYST* MRAM and the company's MRAM solutions in production today.

For more information about Everspin Technologies and its memory solutions, visit **www.everspin.com**.

About Everspin Technologies

Everspin Technologies, Inc., is the world's leading provider of magnetoresistive RAM (MRAM). Everspin MRAM delivers the industry's most robust, highest-performance non-volatile memory for industrial IoT, data centers and other mission-critical applications where data persistence is paramount. Headquartered in Chandler, Arizona, Everspin provides commercially available MRAM solutions to a large and diverse customer base. For more information, visit www.everspin.com.

Cautionary Statement Regarding Forward-Looking Statements

This press release contains forward-looking statements regarding future results that involve risks and uncertainties that could cause actual results or events to differ materially from the expectations disclosed in the forward-looking statements. Forward-looking statements are identified by words such as "expects" or similar expressions. Actual results could differ materially from these forward-looking statements as a result of certain risks and uncertainties, including, without limitation, the risks set forth under the caption "Risk Factors" in Everspin's Annual Report on Form 10-K for the year ended December 31, 2025, filed with the SEC on March 4, 2026, as well as in its subsequent filings with the SEC. Any forward-looking statements made by Everspin in this press release speak only as of the date on which they are made, and subsequent events may cause these expectations to change. Everspin disclaims any obligations to update or alter these forward-looking statements in the future, whether as a result of new information, future events or otherwise, except as required by law.

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